



Features:

- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Floating high-side driver in bootstrap operation to 250V
- 290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal logic and deadtime (100ns) to protect MOSFETs
- Logic input (HIN and LIN) 3.3V capability
- Schmitt triggered logic inputs with internal pull down
- Undervoltage lockout for high and low side drivers
- Extended temperature range:-40°C to +124°C

Description

The TF1304 is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. TF Semiconductor's high voltage process enables the TF1304's high side to switch to 250V in a bootstrap operation.

The TF1304 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. An internal deadtime of 100ns protects high-voltage MOSFETs from shoot-through.

The TF1304 is offered in an 8-pin SOIC narrow package and operates over an extended -40°C to +125°C temperature range.

SOIC-8(N)



Applications

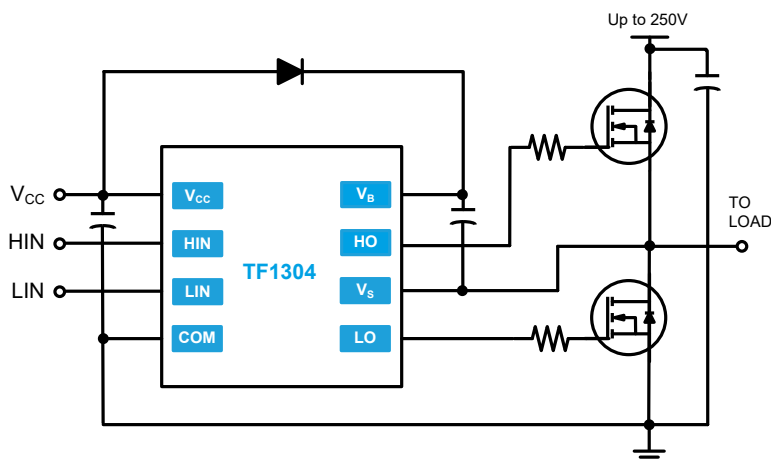
- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

Ordering Information

Year Year Week Week

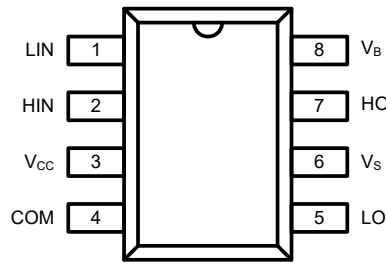
PART NUMBER	PACKAGE	PACKING / Qty	MARK
TF1304-TAU	SOIC-8(N)	Tube / 100	YYWW TF1304 Lot ID
TF1304-TAH	SOIC-8(N)	Tape & Reel / 2500	

Typical Application





Pin Diagrams



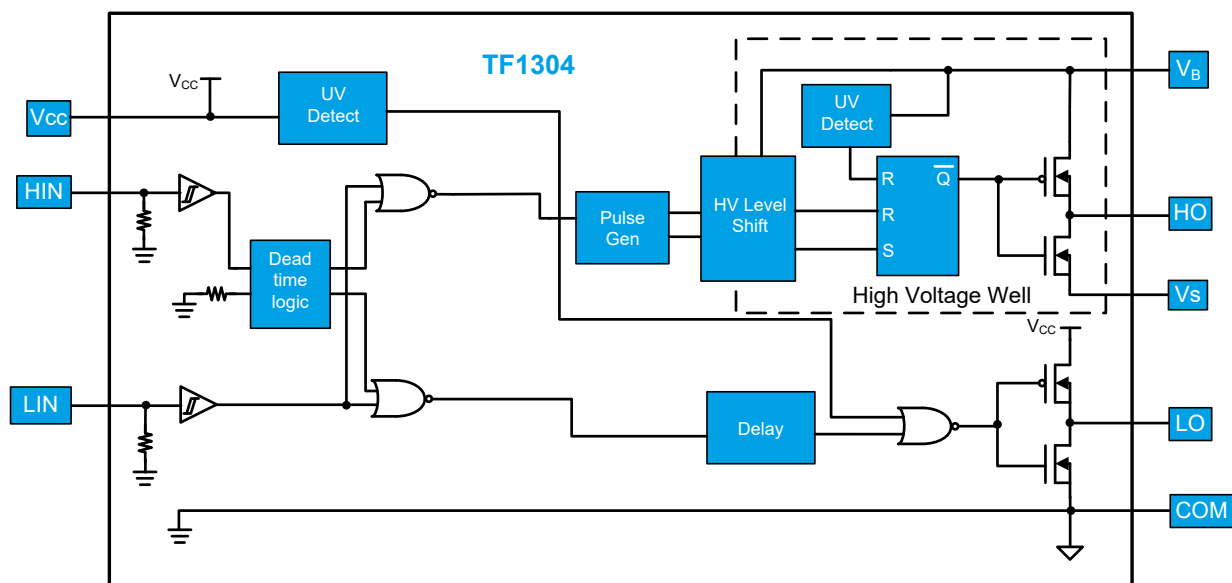
Top View: SOIC-8

TF1304

Pin Descriptions

PIN NAME	PIN DESCRIPTION
HIN	Logic input for high-side gate driver output, in phase with HO
LIN	Logic input for low side gate driver output, in phase with LO
COM	Low-side and logic return
LO	Low-side gate drive output
V _{cc}	Low-side and logic fixed supply
V _s	High-side floating supply return
HO	High-side gate drive output
V _b	High-side floating supply

Functional Block Diagram





Half-Bridge Gate Driver

Absolute Maximum Ratings (NOTE1)

V_B - High side floating supply voltage.....-0.3V to +274V
 V_S - High side floating supply offset voltage..... V_B -24V to V_B +0.3V
 V_{HO} - High side floating output voltage..... V_S -0.3V to V_B +0.3V
 dV_S/dt - Offset supply voltage transient.....50 V/ns

V_{CC} - Low side and logic fixed supply voltage.....-0.3V to +24V
 V_{LO} - Low side output voltage.....-0.3V to V_{CC} +0.3V
 V_{IN} - Logic input voltage (HIN and LIN)..... V_{SS} - 0.3V to V_{CC} +0.3V

P_D - Package power dissipation at $T_A \leq 25^\circ\text{C}$

SOIC-8.....1.25W

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SOIC-8(N) Thermal Resistance (NOTE2)

θ_{JC}25 $^\circ\text{C}/\text{W}$
 θ_{JA}55 $^\circ\text{C}/\text{W}$

T_J - Junction operating temperature+150 $^\circ\text{C}$

T_L - Lead temperature (soldering, 10s) +300 $^\circ\text{C}$

T_{stg} - Storage temperature range-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V_B	High side floating supply absolute voltage	$V_S + 10$	$V_S + 20$	V
V_S	High side floating supply offset voltage	(NOTE 3)	250	V
V_{HO}	High side floating output voltage	V_S	V_B	V
V_{CC}	Low side and logic fixed supply voltage	10	20	V
V_{LO}	Low side output voltage	0	V_{CC}	V
V_{IN}	Logic input voltage	0	5	V
T_A	Ambient temperature	-40	125	$^\circ\text{C}$

NOTE3 Logic operational for V_S of -5 V to +250 V. Logic state held for V_S of -5 V to - V_{BS} .



DC Electrical Characteristics (NOTE4)

V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V_{IH}	Logic "1" input voltage	$V_{CC} = 10V$ to $20V$	2.3			V
V_{IL}	Logic "0" input voltage				0.7	
V_{OH}	High level output voltage, $V_{BIAS} - V_O$	$I_O = 2mA$		0.05	0.2	
V_{OL}	Low level output voltage, V_O	$I_O = 2mA$		0.02	0.1	
I_{LK}	Offset supply leakage current	$V_B = V_S = 250V$			50	μA
I_{BSQ}	Quiescent V_{BS} supply current	$V_{IN} = 0V$ or $5V$	20	60	150	
I_{CCQ}	Quiescent V_{CC} supply current	$V_{IN} = 0V$ or $5V$	50	120	340	μA
I_{IN+}	Logic "1" input bias current	$V_{IN} = 5V$		5	40	μA
I_{IN-}	Logic "0" input bias current	$V_{IN} = 0V$		1.0	5.0	
V_{BSUV+}	V_{BS} supply under-voltage positive going threshold		8.0	8.9	9.8	V
V_{BSUV-}	V_{BS} supply under-voltage negative going threshold		7.4	8.2	9.0	
V_{CCUV+}	V_{CC} supply under-voltage positive going threshold		8.0	8.9	9.8	
V_{CCUV-}	V_{CC} supply under-voltage negative going threshold		7.4	8.2	9.0	
I_{O+}	Output high short circuit pulsed current	$V_O = 0V$, $PW \leq 10ms$	60	290		mA
I_{O-}	Output low short circuit pulsed current	$V_O = 15V$, $PW \leq 10ms$	130	600		

NOTE4 The V_{IN} and I_{IN} parameters are referenced to COM and are applicable to the two logic input pins: HIN and LIN. The V_O and I_O parameters are referenced to COM and are applicable to the respective output pins: HO and LO.



AC Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V and C_L = 1000 pF, and T_A = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t_{ON}	Turn-on propagation delay	$V_S = 0V$		150	210	ns
t_{OFF}	Turn-off propagation delay	$V_S = 0V$ or 250V		150	210	
t_{DMON}	Delay matching HS & LS turn on/off				50	
t_r	Turn-on rise time			70	120	
t_f	Turn-off fall time			35	60	
t_{DT}	Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$		80	100	190	



Timing Waveforms

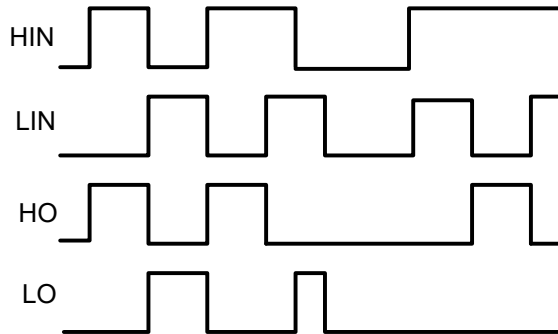


Figure 1. Input / Output Timing Diagram

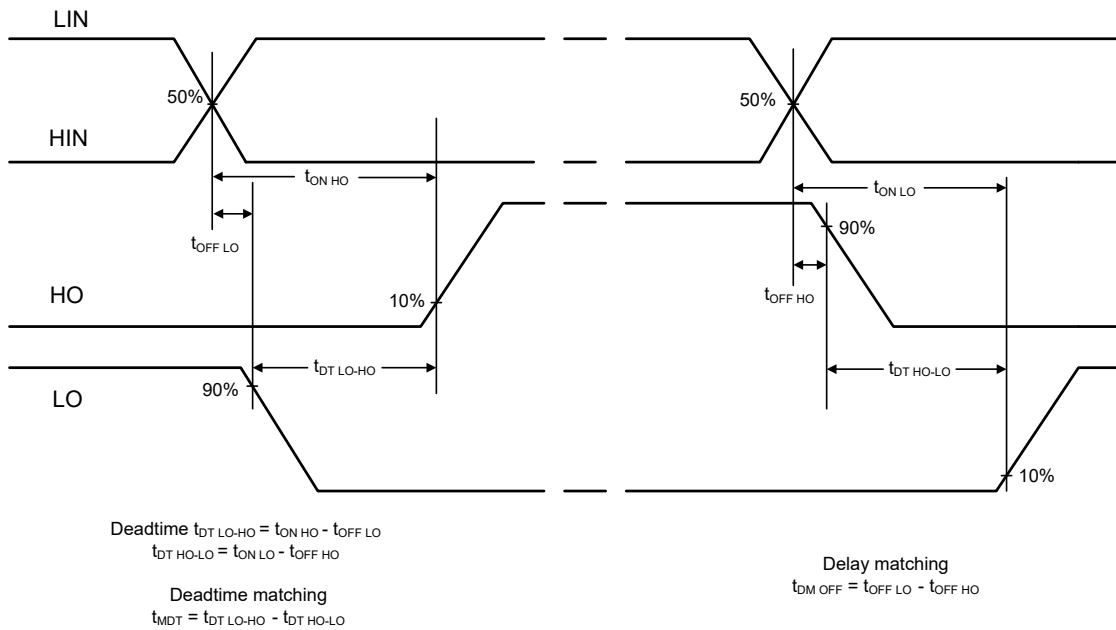
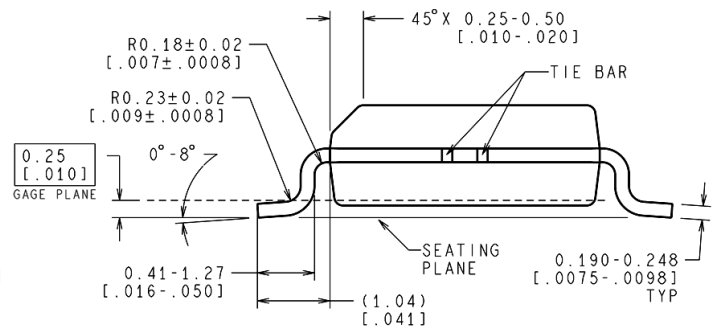
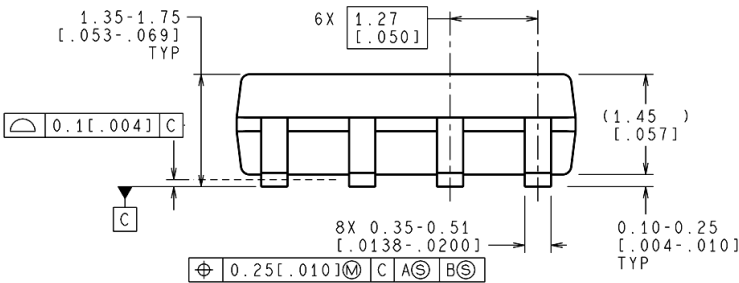
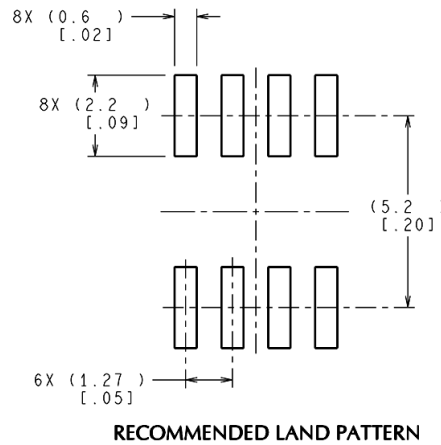
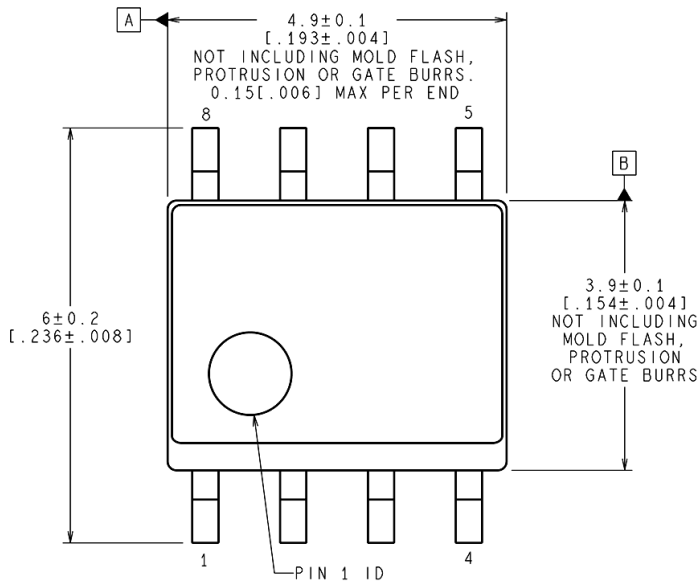


Figure 2. Switching Time Waveform Definition



Package Dimensions (SOIC-8N)

Please contact support@tfsemi.com for package availability.



NOTES: UNLESS OTHERWISE SPECIFIED

1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
 DIMENSIONS IN () FOR REFERENCE ONLY



Revision History

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Keith Spaulding	10/6/2015
1.1	Text edit	Keith Spaulding	7/18/2017

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